

30V PNP MEDIUM POWER TRANSISTOR IN SOT223

Features

- BV_{CEO} > -30V
- I_C = -5.5A High Continuous Collector Current
- I_C = -20A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -140mV @ -1A
- h_{FE} Specified up to -20A for a High Gain Hold-up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

An automotive-compliant part is available under separate datasheet (FZT949Q)

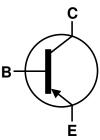
Mechanical Data

- Package: SOT223
- Package Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

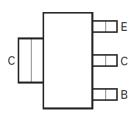
SOT223 (Type DN)



Top View



Device Symbol



Top View Pin-Out

Ordering Information (Note 4)

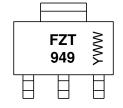
Dout Number	Dookono	Marking	Deal Size (inches)	Tono Width (mm)	Packing	
Part Number	Package	warking	Reel Size (inches)	Tape Width (mm)	Qty.	Carrier
FZT949TA	SOT223 (Type DN)	FZT949	7	12	1,000	Reel

Notes:

- 1, EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant, All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

SOT223 (Type DN)



FZT949 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 3 = 2023) WW or $\overline{W}W$ = Week Code (01 to 53)



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	VcBo	-50	V
Collector-Emitter Voltage	V _{CEO}	-30	V
Emitter-Base Voltage	VEBO	-7	V
Continuous Collector Current	Ic	-5.5	Α
Peak Pulse Current	I _{CM}	-20	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		3.0 24	W	
Linear Derating Factor	(Note 6)	- P _D	1.6 12.8	mW/°C	
Thermal Designance Junction to Ambient	(Note 5)	Reja	42		
Thermal Resistance, Junction to Ambient	(Note 6)	Reja	78	°C/W	
Thermal Resistance, Junction to Lead	(Note 7)	R _{0JL}	8.8]	
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

ESD Ratings (Note 8)

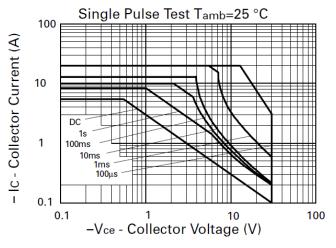
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady state.
- Same as Note 5, except mounted on 25mm x 25mm 1oz copper.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information



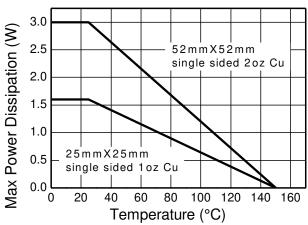
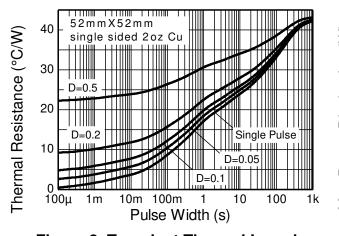


Figure 1. Safe Operating Area

Figure 2. Derating Curve



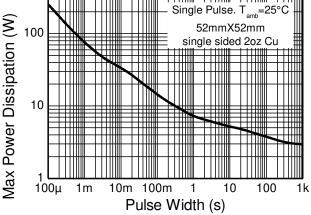


Figure 3. Transient Thermal Impedance

Figure 4. Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-50	-80	_	V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CER}	-50	-80	_	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BVCEO	-30	-45	_	V	Ic = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8	_	V	$I_E = -100\mu A$
Collector Cut-Off Current	I _{CBO}	_	_	-50	nA	V _{CB} = -40V
Condition dat dir darront	IOBO	_	_	-1	μΑ	$V_{CB} = -40V, T_A = +100^{\circ}C$
Collector Cut-Off Current	ICER	_	_	-50	nA	$V_{CE} = -40V, R \le 1k\Omega$
Consider Car Cir Carrotti	IOLIT		_	-1	μΑ	$V_{CE} = -40V, T_A = +100^{\circ}C$
Emitter Cut-Off Current	IEBO	_	_	-10	nA	V _{EB} = -6V
	hFE	100	200	_	-	$I_C = -10$ mA, $V_{CE} = -1$ V
DC Current Transfer Static Ratio (Note 9)		100	200	300		Ic = -1A, VcE = -1V
DC Current Transfer Static Ratio (Note 9)		75	140	_		IC = -5A, VCE = -1V
		_	35	_		$I_C = -20A$, $V_{CE} = -2V$
	VCE(sat)	_	-50	-75	mV	$I_C = -500 \text{mA}, I_B = -20 \text{mA}$
Collector-Emitter Saturation Voltage (Note 9)		_	-85	-140		$I_C = -1A$, $I_B = -20mA$
Collector-Enritter Saturation Voltage (Note 9)		_	-190	-270		$I_C = -2A$, $I_B = -200mA$
		_	-350	-440		$I_C = -5.5A$, $I_B = -500mA$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	_	-1,100	-1,250	mV	$I_C = -5.5A$, $I_B = -500mA$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(on)}	_	-900	-1,060	mV	Ic = -5.5A, VcE = -1V
Transitional Frequency (Note 9)	f _T	_	100	_	MHz	$I_C = -100$ mA, $V_{CE} = -10$ V $f = 50$ MHz
Output Capacitance	Cobo	_	122	_	pF	V _{CB} = -10V, f = 1MHz
Switching Time	ton	_	120	_	nc	Vcc = -10V, Ic = -4A
Switching Time	toff	_	130	_	ns	$I_{B1} = -I_{B2} = -400 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

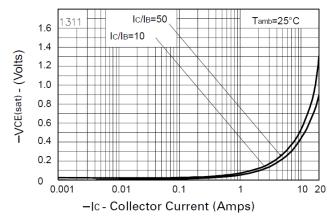


Figure 5. $V_{\text{CE(sat)}} v I_{\text{C}}$

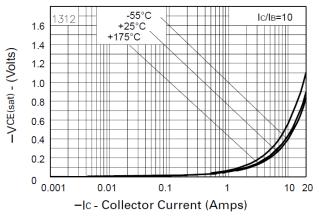


Figure 6. V_{CE(sat)} v I_C

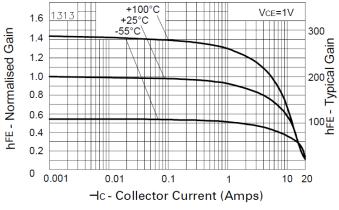


Figure 7. hfe v lc

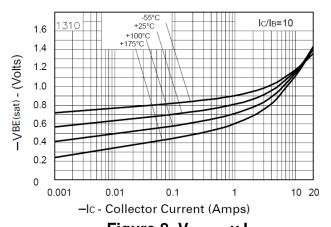


Figure 8. V_{BE(sat)} v I_C

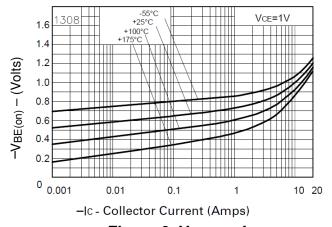


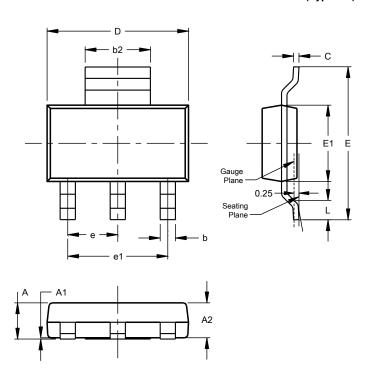
Figure 9. VBE(on) v Ic



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)

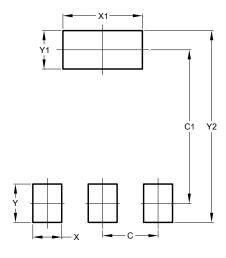


SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A 1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10	-		
С	0.20	0.32			
D	6.30	6.70			
Е	6.70	7.30			
E1	3.30	3.70			
е			2.30		
e1	-		4.60		
L	0.85				
All Dimensions in mm					

Suggested Pad Layout

 $Please \ see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$

SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
V2	8 00



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